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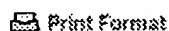
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Pages:2790 - 2795[\[Abstract\]](#) [\[PDF Full-Text \(152 KB\)\]](#) **IEEE JNL****2 MOSFET gate leakage modeling and selection guide for alternative gate dielectrics based on leakage considerations***Yee-Chia Yeo; Tsu-Jae King; Chenming Hu;*Electron Devices, IEEE Transactions on , Volume: 50 , Issue: 4 , April 2003
Pages:1027 - 1035[\[Abstract\]](#) [\[PDF Full-Text \(756 KB\)\]](#) **IEEE JNL****3 Scaling effects on gate leakage current***Watanabe, H.; Matsuzawa, K.; Takagi, S.;*Electron Devices, IEEE Transactions on , Volume: 50 , Issue: 8 , Aug. 2003
Pages:1779 - 1784[\[Abstract\]](#) [\[PDF Full-Text \(471 KB\)\]](#) **IEEE JNL****4 Modeling of direct tunneling gate current in ultra-thin gate oxide MOSFETs: a comparison between simulators***Cassan, E.; Galdin, S.; Dollfus, P.; Hesto, P.;*Simulation of Semiconductor Processes and Devices, 1999. SISPAD '99. 1999 International Conference on , 6-8 Sept. 1999
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6 Direct tunneling gate leakage current in transistors with ultrathin silicon nitride gate dielectric

Yee Chia Yeo; Qiang Lu; Wen Chin Lee; Tsu-Jae King; Chenming Hu; Xiewen Wang; Xin Guo; Ma, T.P.;

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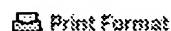
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